Diode Laser Based Trace Gas Sensors for Semiconductor Process Monitoring

F. Tittel, D. Leleux, H. Tanaka, R. Claps, F. Englich, M. Erdelyi Rice Quantum Institute Rice University Houston, TX, USA

Summary

The development of compact, robust diode laser based gas sensor that are potentially more effective than presently available monitoring instruments and their application to precise, real-time monitoring and quantification of process gases (such as HCl, NH₃, and HF) used in semiconductor manufacturing will be reported. Critical manufacturing steps include chemical vapor deposition and plasma etching [1] and also the monitoring of internal clean room air quality, as well as external plant emissions at parts-per-billion (ppb) levels. This becomes particularly important as device feature sizes approach the 100 nm level and below, where extremely thin films are required and variations in process gas concentrations will significantly impact integrated circuit (IC) device yields. Several recent advances in enabling technologies that include commercially available telecommunications laser diodes, optical fiber technology (beam delivery, couplers, and amplifiers), and novel digital signal processing (DSP) techniques will be utilized in sensor based laser absorption spectroscopy.

Three types of gas sensor architectures are being studied: near infrared distributed feedback (DFB) diode lasers for overtone spectroscopy, mid-infrared spectroscopic sources based on difference frequency generation (DFG), and quantum cascade lasers for direct absorption of ro-vibrational transitions of fundamental molecular absorption bands. Details of extractive NH₃ monitoring by all three techniques will be described.

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F. K. Tittel, D. Leleux, R.Claps, F.Englich & T.Harman Rice University, Houston TX, USA fkt@rice.edu http://www.ruf.rice.edu/~lasersci/

